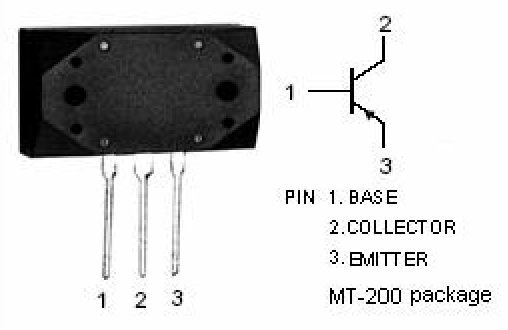
Silicon PNP Power Transistor **2SA1216**



DESCRIPTION

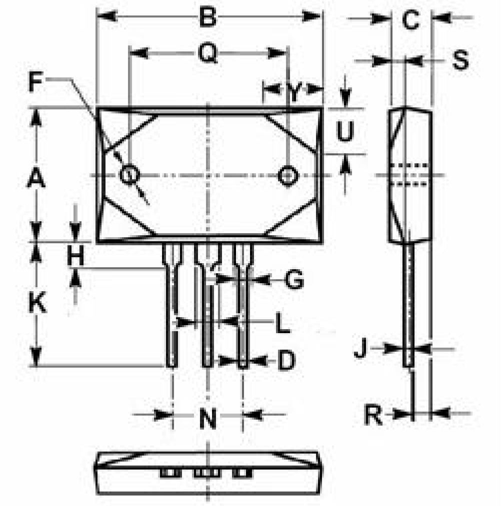
- High Collector-Emitter Breakdown Voltage- $V_{(BR)CEO}$= -180V(Min)
- Good Linearity of h_{FE}
- Complement to Type 2SC2922

APPLICATIONS

- Designed for audio and general purpose applications.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-180	V
V_{CEO}	Collector-Emitter Voltage	-180	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-17	A
I_B	Base Current-Continuous	-5	A
P_C	Collector Power Dissipation @ T_C=25℃	200	W
T_J	Junction Temperature	150	℃
T_{stg}	Storage Temperature Range	-55~150	℃



DIM	mm	
	MIN	MAX
A	21.30	21.70
B	36.10	36.70
C	5.80	6.20
D	1.04	1.07
F	3.10	3.30
G	1.90	2.10
H	3.80	4.00
J	0.55	0.85
K	20.00	20.30
L	2.90	3.10
N	10.70	11.10
Q	24.00	24.40
R	2.90	3.30
S	2.00	2.20
U	6.90	7.10
Y	8.90	9.10

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	I_C= -25mA ; I_B= 0	-180			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	I_C= -8A; I_B= -0.8A			-2.0	V
I_{CBO}	Collector Cutoff Current	V_{CB}= -180V; I_E= 0			-100	μA
I_{EBO}	Emitter Cutoff Current	V_{EB}= -5V; I_C=0			-100	μA
h_{FE}	DC Current Gain	I_C= -8A; V_{CE}= -4V	30		180	
C_{OB}	Output Capacitance	I_E= 0; V_{CB}= -10V;f_{test}= 1.0MHz		500		pF
f_T	Current-Gain—Bandwidth Product	I_E= 2A; V_{CE}= -12V		40		MHz

Switching times

t_{on}	Turn-on Time	I_C= -10A ,R_L= 4Ω , I_{B1}= -I_{B2}= -1A,V_{CC}= -40V		0.3		μs
t_{stg}	Storage Time			0.7		μs
t_f	Fall Time			0.2		μs

u h_{FE} Classifications

O	Y	P	G
30-60	50-100	70-140	90-180